附錄二　CREE 產品與重要里程碑整理[1]

1980s	
1987/7	Cree founded
1989/8	**Introduced first blue LED**
1990s	
1991/10	**Released world's first commercial SiC wafers**
1993/2	**Initial public offering**
1993/8	Introduced 4H SiC wafer
1993/9	**Introduced brighter version blue LED**
1993/10	Developed SiC microwave transistors operating up to 12.9 GHz
1995/6	Introduced Nitride-based blue LED
1997/5	Announced reduced micropipe 4 HN SiC wafers
1997/6	Demonstrated pulsed GaN blue laser at room temperature
1997/9	Introduced 2-inch SiC wafer
1998/3	Demonstrated high-power microwave SiC MESFET
1999/5	**Introduced InGaN blue and green LEDs**
1999/6	Introduced 48 V, 10 W SiC MESFET RF device
1999/10	Demonstrated 4-inch SiC wafer
2000	
2000/5	Demonstrated 12.3 kV high-efficiency SiC power rectifier
2000/6	**Introduced lower-current InGaN blue and green LEDs**
2000/8	Announced high-power 10 GHz GaN HEMT
2000/10	Introduced UltraBright® blue and green LEDs
2001	
2001/2	Demonstrated 32-percent quantum efficiency with near-UV LED
2001/4	Introduced 3-inch 4H SiC wafers
2001/5	Introduced MegaBright® blue LED

[1] 參見 Cree 公司網站，http://www.cree.com/index.asp。

2001/6	Introduced 4H and 6H 3-inch SiC wafers
2001/6	Introduced first SiC Schottky diodes
2001/6	**Introduced 12 mW UV LEDs**
2001/10	Introduced XBright® blue LED
2001/11	Introduced green 505 MegaBright LED
2001/11	Announced blue laser lifetimes in excess of 1,000 hours
2001/12	Demonstrated 108 W at 2 GHz from GaN RF devices
2002	
2002/1	Introduced 10-A, 600-V, SiC Schottky rectifier (SiC-based power products)
2002/1	Introduced green 525 MegaBright LED
2002/2	Introduced XBright power chip
2002/8	Introduced 20-A, 600-V, Zero Recovery® SiC rectifier
2003	
2003/2	Released 1200 V SiC Schottky rectifier
2003/3	Introduced second-generation SiC MESFET RF transistor
2003/6	Introduced MegaBright Plus™ and XBright Plus™ blue LEDs
2003/6	Introduced LDMOS products for avionics and radar markets
2003/6	Demonstrated 100 mm semi-insulating SiC substrates
2003/7	Introduced RazerThin® LED products
2004 (high power)	
2004/1	Expanded XThin® LED product family
2004/5	Launched brighter XThin LED product
2004/7	Launched XLamp® LED product line
2004/11	Announced XLamp 7090
2005	
2005/2	**Achieved standard LED efficiency of 100 lumens/watt in R&D**
2005/2	Achieved 56 lumens from one-watt white XLamp LED in R&D
2005/5	Introduced brighter blue and green XB900™ power LEDs for LCD BL
2005/5	Introduced Colorwave™ backlight solution for LCD TVs & monitors

2005/6	Introduced MegaBright 290 Gen 2 LED Product
2005/6	Introduced RazerThin 230 LED product
2005/6	Introduced SiC MESFETS for WiMAX power amplifiers
2005/7	**Introduced 3-watt XLamp**
2005/9	**Achieved 70 lumens per watt with XLamp 7090 LED in R&D**
2005/9	Introduced 100mm (4”) SiC substrate and epitaxy material
2006	
2006/1	Demonstrated a 100-kVA SiC Three Phase Inverter
2006/2	Introduced the XR series of XLamp LEDs
2006/3	Introduced the EZBright™ family of LED chips
2006/4	Introduced the EZR™ LED chip for the EZBright family
2006/5	Introduced GaN HEMT for WiMAX power transistors
2006/6	**Demonstrated a 131-lumens/watt white LED**
2006/6	Demonstrated 400 watts of RF power for GaN S-Band transistors
2006/7	Introduced 2-amp rectifier for PC power supplies
2006/8	Introduced EZBright1000™ LED power chip for general lighting applications
2006/10	**Delivered the XLamp XR-E Series LED, the first 160-lumen white power LED**
2007	
2007/2	Introduced the XLamp XR-C series of LEDs
2007/2	Introduced the EZBright700 LED power chip
2007/3	Expanded the XLamp XR-E and XR-C series of LEDs with warm white color temperatures
2007/4	**Acquired COTCO Luminant Device Ltd. of Hong Kong**
2007/5	Demonstrated 100-mm, Zero Micropipe SiC substrates
2007/6	Introduced GaN HEMT for broadband applications
2007/6	Introduced blue XLamp XR-E LEDs
2007/6	**Announced commercial availability of XLamp LEDs with minimum luminous flux of 100 lumens at 350 mA**
2007/9	Achieved 1,000 lumens from a single LED

2007/10	Introduced 8-A, 600-V, Zero Recovery SiC rectifier for computer servers
2007/10	Announced commercial release of 100-mm, Zero Micropipe SiC substrates